

INDEX

- absorption, 23, 35, 224
 - band-to-band, 345, 369
- absorption coefficient, 130, 242–243, 250
 - intensity-dependent, 351
 - of direct-gap semiconductor, 346
 - of indirect-gap semiconductor, 346
 - of waveguide mode, 131
 - unsaturated, 351
- absorption cross section, 238, 250
 - pump, 254
- absorption saturation, 351
- absorption transition, 236
- absorptive external modulation, 344
- absorptive modulation, 297, 305
 - all-optical, 340, 345, 350
 - external, 344
- AC conductivity, 39
- acoustic
 - frequency, 52
 - normal mode, 53
 - longitudinal, 53
 - quasi-longitudinal, 53
 - quasi-transverse, 53
 - transverse, 53
- wave, 52
 - longitudinal, 53
 - standing, 53
 - transverse, 53
 - traveling, 52
- wavelength, 52
- acousto-optic amplitude modulation, 334
- acousto-optic diffraction
 - Bragg, 334
 - order, 333
 - Raman–Nath, 334
- acousto-optic effect, 52
- acousto-optic modulation, 297, 320, 333
- acousto-optic modulator
 - standing-wave, 338
 - traveling-wave, 336
- acousto-optic polarization modulation, 333
- active region
 - of photodiode, 372
- all-optical absorptive modulation, 340, 345, 350
- all-optical dispersive modulation, 340
- all-optical modulation, 297, 320, 340, 350
- all-optical phase modulation, 342
- all-optical polarization modulation, 342
- all-optical refractive modulation, 340
- all-optical switching, 340
- AM, 298, *See* amplitude modulation
- Ampere’s law, 4
- amplification, 23
 - of optical field, 241
- amplification coefficient, 130, 242
 - of waveguide mode, 131
- amplification factor
 - round-trip, 207, 274
- amplified spontaneous emission, 269
- amplitude modulation, 297–298, 305, 309, 320, 326, 344
 - acousto-optic, 334
 - analog, 305–306
 - digital, 305–306
 - electro-optic, 326
 - magneto-optic, 329
- amplitude modulator, 326
- amplitude-shift keying, 298, 305, *See* ASK
 - binary, 305
- analog amplitude modulation, 305–306
- analog frequency modulation, 300, 333
- analog modulation, 297–298, 306, 310, 314
- analog polarization modulation, 302
- analyzer, 326
- angle
 - of diffraction, 335
 - of incidence, 94, 335
 - of reflection, 94
 - of refraction, 94
- angular frequency, 1
- anisotropic crystal, 28
- anisotropic medium, 24, 77
- anisotropy, 24
- anomalous dispersion, 36, 122
- antiferromagnetic material, 49
- antiferromagnetic material, 49
- antiguide factor, 294
- ASK, 298, 305, *See* amplitude-shift keying
- asymmetric coupling, 144, 146, 160
- asymmetric waveguide, 118
- attenuation
 - of optical field, 241
- attenuation coefficient, 130, 242
 - of waveguide mode, 131
- attenuation factor
 - round-trip, 207
- autocorrelation theorem, 407
- axial vector, 6
- bandgap, 365
 - of photoconductor, 369
 - of quantum well, 347
 - of semiconductor, 346, 365, 371
- band-to-band absorption, 345, 369
- band-to-band transition, 37
- bandwidth, 122
 - 3-dB, 311, 317, 390
 - gain, 240, 281, 283
 - modulation. *See* modulation bandwidth
 - of detection system, 363, 379
 - of LED, 311
 - of photodetector. *See* photodetector bandwidth
 - of semiconductor laser, 317
- beam waist, 88
- BFSK. *See* binary frequency-shift keying
- biaxial crystal, 29, 77
- binary amplitude-shift keying, 305
- binary frequency-shift keying, 300
- binary phase-shift keying, 300
- binary polarization-shift keying, 302
- birefringence, 28
 - circular, 31, 52
 - electrically induced, 48
 - linear, 28, 52
 - magnetically induced, 52
 - optical-field-induced, 342
- birefringent crystal, 28
- blackbody radiation, 235, 379
- bleached condition, 257
- bottleneck factor, 251, 256–257, 260
- boundary conditions, 7, 67
- BPolSK. *See* binary polarization-shift keying
- BPSK. *See* binary phase-shift keying
- Bragg angle, 335
- Bragg diffraction, 334
 - down-shifted, 335
 - up-shifted, 335

- Brewster angle, 96
- Brewster window, 97
- bulk modulator, 297
- carrier frequency, 3, 12, 19, 123, 300–301, 305
- carrier injection efficiency, 309
- carrier relaxation rate
 - differential, 315
 - nonlinear, 315
 - spontaneous, 315
 - total, 316
- carrier wavevector, 19
- causality, 22, 44
- causality condition, 34
- cavity
 - cold, 214
 - Fabry–Pérot, 204
 - finesse, 209
 - folded, 204
 - laser, 216
 - length, 206
 - linear, 204, 206, 212
 - non-Fabry–Pérot, 204
 - optical, 204
 - passive, 207
 - resonance condition, 209, 211
 - ring, 204, 206, 212
- cavity decay rate, 214, 315
 - of Fabry–Pérot cavity, 219
- cavity lifetime, 214
- centrosymmetric, 46, 58
 - material, 32, 45, 51, 59
- charge carrier
 - excess, 308, 368
 - free, 5, 38, 104
 - number, 363
 - photogenerated, 363, 368, 376–377, 382
 - positive, 32, 38
- charge density, 4
- charge-coupled device, 363
- chromatic dispersion, 122
- circular birefringence, 31
 - magnetic, 31
 - magnetically induced, 52, 328
 - natural, 31
- circular dichroism, 31
 - magnetic, 31
 - magnetically induced, 52
 - natural, 31
- circular polarization, 16, 25
- circularly polarized, 14
 - left, 16
 - right, 16
- codirectional coupling, 154
- coherence, 173
 - spatial, 173
 - temporal, 173
- cold cavity, 214
- collection efficiency, 382
- complex field, 11
- complex field amplitude, 18
- conduction current, 5, 38
- conduction electron, 32
- conduction susceptibility, 39
- conductivity
 - AC, 39
 - dark, 368
 - DC, 39
 - of photoconductor, 368
 - of semiconductor, 368
 - optical, 38
- confocal parameter, 88
- conservation of charge, 5
- conservation of power, 159
- constructive interference, 171, 204
 - complete, 171
 - partial, 171
- continuity equation, 5
- contradirectional coupling, 156
- convolution integral, 407
- correlation theorem, 407
- Cotton–Mouton effect, 52
- Coulomb’s law, 5
- coupled-mode equations, 143
 - for multiple substructures, 146
 - for single structure, 143
 - for two-mode coupling, 147
 - codirectional, 154
 - contradirectional, 156
- coupled-mode theory, 141
- coupler
 - 3-dB, 182, 327
 - asymmetric, 149
 - directional, 147, 149, 182
 - grating, 151
 - symmetric, 149
 - waveguide, 151
 - Y-junction, 182, 327
- coupling coefficient, 143, 146, 161, 164
 - for multiple-structure coupling, 146
 - two modes, 148
 - for periodic structure, 150
 - for single-structure coupling, 143
 - q*th order, 150
 - self, 149
- coupling efficiency, 155, 157, 190, 306
 - for codirectional coupling, 155
 - perfectly phase-matched, 161
 - phase-mismatched, 163
 - for contradirectional coupling, 157
 - perfectly phase-matched, 161
 - phase-mismatched, 163
- coupling length, 156
 - perfectly phase-matched, 161
 - phase-mismatched, 163
- critical angle, 97
- critical fluorescence power, 268
- critical fluorescence power density, 268
- cross modulation, 340
- cross section
 - absorption, 238, 250
 - emission, 238, 250
 - transition, 238
- cross-phase modulation, 342
- crystal
 - anisotropic, 28
 - biaxial, 29
 - birefringent, 28
 - cubic, 29
 - hexagonal, 30
 - monoclinic, 30
 - negative uniaxial, 28
 - orthorhombic, 30
 - positive uniaxial, 28
 - structural symmetry, 29
 - tetragonal, 30
 - triclinic, 30
 - trigonal, 30
 - uniaxial, 28
- crystal axis, 29
- crystal system, 46, 58
- Curie temperature, 49
- current
 - conduction, 5, 38
 - dark, 378
 - displacement, 5
 - induced, 5, 38
- current density, 4
- current modulation, 345
 - direct, 308
- cutoff frequency
 - 3-dB, 390
 - of guided mode, 117
 - of surface plasmon mode, 106
- cutoff wavelength
 - of guided mode, 117
 - of surface plasmon mode, 106
- dark conductivity, 368
- dark current, 378
- DC conductivity, 39
- degeneracy
 - in energy level, 224, 251
- degeneracy factor, 224, 236
- degenerate semiconductor, 365
 - n-type, 365
 - p-type, 365
- depletion layer, 371

- destructive interference, 171
 - complete, 171
 - partial, 172
- detectivity, 386
 - specific, 369, 386
- detector
 - photoconductive, 368
 - photoemissive, 363
 - photon, 362
 - quantum, 362
 - square-law, 362
 - thermal, 362
- diamagnetic material, 49
- dichroism, 28
 - circular, 31, 52
 - electrically induced, 48
 - linear, 28, 52
 - magnetically induced, 52
- dielectric constant
 - principal, 28
 - tensor, 28
- differential carrier relaxation rate, 315
- differential gain parameter, 315
- differential phase modulation, 302, 324, 326, 329
- differential power conversion efficiency, 291
- diffraction modulation, 297, 299, 307, 333
- diffraction order, 184–185
 - reflective, 188
 - transmissive, 185, 188
- diffusion current, 372
- diffusion region, 371
- digital amplitude modulation, 305–306
- digital frequency modulation, 300, 333
- digital modulation, 297–298, 350
- digital polarization modulation, 302
- direct current-modulation, 308
- direct modulation, 297, 299, 305, 308, 345
- direct-gap semiconductor, 249, 346, 369
- directional coupler, 147, 149, 182
 - asymmetric, 149
 - symmetric, 149
 - two-channel, 149
- discrete energy level, 32
- dispersion, 122
 - anomalous, 36, 122
 - chromatic, 122
 - frequency, 23
 - group-velocity, 124
 - coefficient, 124
 - effective, 126
 - negative, 124
 - positive, 124
 - intermode, 122, 127
 - intramode, 122, 127
 - material, 122, 126
 - modal, 115, 117, 122, 127
 - mode-order, 128
 - momentum, 23
 - normal, 36, 122
 - of surface plasmon mode, 106
 - phase-velocity, 122
 - polarization, 117, 122, 127
 - polarization-mode, 128
 - waveguide, 122, 126
- displacement current, 5
- distributed feedback, 204
- distributed feedback laser, 275
- distributed loss, 218, 276
- divergence angle, 86, 88
- Doppler broadening, 231
- Doppler effect, 230
- double refraction, 98
- double-slit interference, 176
- drift current, 371–372
- Drude model, 38, 62
- dynamic range of photodetector, 387–388
- effective group index, 126
- effective group-velocity dispersion, 126
- effective mass, 32, 38, 347
- effective population inversion, 250
- effective refractive index, 126
 - of waveguide mode, 112
- effective waveguide thickness
 - for guided TE mode, 114
 - for guided TM mode, 115
- EH mode, 69
- Einstein A coefficient, 226, 234
- Einstein B coefficient, 234
- elastic wave, 52
- elasto-optic coefficient, 53
- electric displacement, 4
- electric field, 4
 - complex, 12, 18, 169
- electric permittivity, 4, 7
 - of free space, 4
 - tensor, 7
- electric polarization, 4, 7
- electric susceptibility, 7
 - tensor, 7
- electric-dipole approximation, 58
- electric-dipole interaction, 59
- electric-dipole operator, 33
- electro-absorption modulation, 345
- electro-absorption modulator, 345, 349
- electromagnetic field, 4
- electron
 - bound, 32
 - conduction, 32
 - free, 32
 - valence, 32
- electron affinity, 363
- electron mobility, 368
- electro-optic amplitude modulation, 326
- electro-optic coefficient
 - linear, 45
 - quadratic, 45
- electro-optic effect, 44
 - first order, 45
 - linear, 45
 - quadratic, 45
 - second order, 45
- electro-optic Kerr coefficient, 45, 59
- electro-optic Kerr effect, 45
- electro-optic modulation, 297, 320
- electro-optic modulator, 320
- electro-optic phase modulation, 321, 328
- electro-optic polarization modulation, 324
- elliptic polarization, 14, 25
- elliptically polarized, 14
- ellipticity, 14
- emission
 - spontaneous, 224
 - stimulated, 35, 224
- emission cross section, 238, 250
 - homogeneously broadened medium, 239
 - inhomogeneously broadened medium, 239
 - pump, 254
- energy band, 32
- energy density
 - of optical radiation, 234
- energy level, 249
 - ground, 255
 - lower, 224
 - upper, 224
 - vacuum, 363
- envelope, 19, 123
- Er: fiber, 239
- etalon, 191
- evanescent radiation mode, 111
- excess noise factor, 378
- excess shot noise, 378
- exciton, 345
 - free, 348
- external modulation, 297
 - absorptive, 344
 - refractive, 319
- external modulator, 306
- external photoelectric effect, 362–363
- external quantum efficiency
 - of LED, 309
 - of photodetector, 363, 382
 - of photodiode, 372
 - of semiconductor laser, 314
- external reflection, 96
- extinction ratio, 307
- extraordinary index, 28

- extraordinary wave, 81
 - extrinsic photoconductivity, 369
 - extrinsic photoconductor
 - n-type, 369
 - p-type, 369
 - extrinsic semiconductor, 369
 - Fabry–Pérot cavity, 204, 216
 - stability criterion, 216
 - Fabry–Pérot etalon, 191
 - Fabry–Pérot interferometer, 178, 191, 204, 209
 - Fabry–Pérot laser, 275
 - falltime, 389
 - Faraday effect, 52, 329–330
 - Faraday rotation, 329–330
 - sense, 331
 - specific, 330
 - Faraday rotator, 330
 - Faraday’s law, 4
 - fast axis, 80
 - Fermi level, 363, 365
 - ferrimagnetic material, 49
 - ferromagnetic material, 49
 - field amplitude
 - complex, 18
 - scalar, 18
 - vectorial, 12, 18
 - filling factor
 - of gain medium, 206
 - finesse, 194, 209
 - of lossless Fabry–Pérot interferometer, 193, 219
 - of lossy Fabry–Pérot cavity, 219
 - of optical cavity, 209
 - flat interface, 190
 - fluorescence, 226
 - fluorescence lifetime, 227, 239, 250
 - FM, 298. *See* frequency modulation
 - folded cavity, 204
 - forward-coupling matrix, 154, 161
 - Fourier-transform relations, 13, 406
 - four-level system, 256, 259–260
 - ideal, 256
 - Franz–Keldysh effect, 345–346
 - free spectral range, 194, 210
 - frequency chirping, 129, 309
 - negative, 129
 - positive, 129
 - frequency dispersion, 23
 - frequency modulation, 297–298, 300, 309
 - analog, 300, 333
 - digital, 300, 333
 - frequency response
 - of LED, 311
 - of photodetector, 389
 - of semiconductor laser, 316
 - frequency-shift keying, 298. *See* FSK
 - binary. *See* BFSK
 - quadrature. *See* QFSK
 - Fresnel equations, 95
 - FSK, 298. *See* frequency-shift keying
 - fundamental mode, 109, 118, 121
 - gain bandwidth, 240, 281, 283
 - gain coefficient, 130, 242, 244, 250, 259
 - of waveguide mode, 131
 - small-signal, 263
 - unsaturated, 259, 263
 - gain compression, 315
 - gain factor
 - round-trip, 207, 274
 - gain filling factor, 206
 - gain parameter, 286
 - differential, 315
 - nonlinear, 315
 - of gain medium, 286
 - of laser mode, 286
 - of semiconductor laser, 315
 - saturated, 287
 - unsaturated, 287
 - gain saturation, 264, 281–282, 351
 - Gauss’s law, 5
 - Gaussian beam, 87
 - complex radius of curvature, 90
 - confocal parameter, 88
 - divergence angle, 86, 88
 - radius of curvature, 88
 - Rayleigh range, 88
 - spot size, 86, 88
 - waist, 88
 - Gaussian lineshape, 231
 - Gaussian mode, 86, 211
 - basis for linear expansion, 89, 92
 - orthonormality relation, 87
 - propagation constant, 87
 - graded-index waveguide, 108
 - grating, 151, 183
 - at interface, 187
 - one-dimensional, 151
 - period, 153
 - sinusoidal, 152
 - square-function, 153
 - surface, 189
 - transmission, 183
 - transmissive diffraction, 183–184
 - grating waveguide coupler, 151
 - ground level, 255
 - group index, 124
 - effective for waveguide mode, 126
 - group IV semiconductor, 367
 - group velocity, 122–123
 - of waveguide mode, 127
 - group-velocity dispersion, 124
 - coefficient, 124
 - effective for waveguide mode, 126
 - negative, 124
 - positive, 124
- guided mode, 109, 112
 - cutoff condition, 117, 121
 - cutoff frequency, 117
 - cutoff wavelength, 117
 - fundamental, 109, 118, 121
 - high-order, 109
 - number, 109, 118, 121
 - half-wave plate, 80
 - half-wave voltage, 322
 - harmonic field, 11
 - HE mode, 69
 - Heaviside step function, 406
 - helicity
 - negative, 17
 - positive, 16
 - Helmholtz equation, 86
 - Hermite polynomial, 90
 - Hermite–Gaussian function, 89
 - Hermite–Gaussian mode, 90
 - high-order mode, 109
 - hole mobility, 368
 - homogeneous broadening, 225
 - homogeneous region, 371
 - homogeneous system, 225
 - homogeneously broadened laser, 280
 - hybrid mode, 69, 108
 - IM, 305. *See* intensity modulation
 - impulse response, 389
 - index contraction, 45
 - index ellipsoid, 82
 - index of refraction, 76
 - complex, 129
 - effective for waveguide mode, 112
 - extraordinary, 28
 - for extraordinary wave, 82
 - for ordinary wave, 82
 - intensity-dependent, 342
 - ordinary, 28
 - principal, 28
 - indirect-gap semiconductor, 346, 369
 - induced transition, 224
 - induced transition rate, 235
 - inhomogeneous broadening, 230
 - inhomogeneous system, 230
 - inhomogeneously broadened laser, 282
 - intensity, 2
 - light, 12–13
 - of normal mode, 71
 - of optical field, 130
 - intensity modulation, 305

- intensity-dependent absorption coefficient, 351
- intensity-dependent index change, 342
- intensity-dependent index of refraction, 342
- interaction length, 161, 164–165, 334
- interband transition, 37
- interface mode, 92
- interference
 - constructive, 171, 204
 - complete, 171
 - partial, 171
 - destructive, 171
 - complete, 171
 - partial, 172
 - double-slit, 176
 - of two fields, 169
- interference filter, 199
- interference fringe, 173, 175
 - bright, 175
 - dark, 175
- interferometer
 - Fabry–Pérot, 178, 191
 - Mach–Zehnder, 178, 180
 - Michelson, 178
- intermode dispersion, 122, 127
- internal gain
 - of photodetector, 363
- internal photoelectric effect, 362
- internal quantum efficiency
 - of LED, 311
 - of photodetector, 382
- internal reflection, 96
 - total, 97, 99
- intraband transition, 38
- intracavity energy growth rate, 286
 - threshold, 286
- intracavity photon density, 286
- intracavity photon growth rate, 286
- intramode dispersion, 122, 127
- intrinsic photoconductivity, 369
- intrinsic responsivity, 384
- inversion symmetry, 45
- irradiance, 12
- isotropic material, 46
- isotropic medium, 24, 75
- Johnson noise, 375
- junction photodiode, 363, 371
 - photoconductive mode, 373–374
 - photovoltaic mode, 373
- K* factor, 316
- Kerr effect
 - electro-optic, 45
 - magneto-optic, 52, 329
 - optical, 342
- Kerr-lens mode locking, 342
- Kramers–Kronig relations, 44
- Laguerre–Gaussian function, 90
- Laguerre–Gaussian mode, 90
- laser, 274
 - homogeneously broadened, 280
 - inhomogeneously broadened, 282
 - longitudinal mode, 280, 282
 - transverse mode, 280, 282
- laser amplifier, 265
- laser cavity, 216
- laser level
 - lower, 250, 253, 255
 - upper, 250, 253, 255
- laser linewidth, 283
- laser oscillation, 274
 - condition, 274
 - gain condition, 275
 - phase condition, 275
- laser oscillator, 274
- laser power, 285
- laser system
 - four-level, 256, 259–260
 - ideal four-level, 256
 - quasi-two-level, 254, 259
 - three-level, 255, 259–260
 - two-level, 253
- laser threshold, 276
- laser transition, 218, 275
- LED, 297, 308–309, *See* light-emitting diode
- left-circular polarization, 16
- L–I* characteristics
 - of LED, 309
 - of semiconductor laser, 314
- lifetime
 - cavity, 214
 - fluorescence, 227
 - of energy level, 226
 - photon, 214
 - saturation, 259
 - spontaneous radiative, 226, 236
- lifetime broadening, 226
- light intensity, 12–13
- light-current characteristics
 - of LED, 309
 - of semiconductor laser, 314
- light-emitting diode, 297, 309, *See* LED
- line filter, 199
- linear birefringence, 28, 48
 - electrically induced, 48
 - magnetically induced, 52
- linear cavity, 204, 206, 212
- linear dichroism, 28, 48
 - electrically induced, 48
 - magnetically induced, 52
- linear medium, 24
- linear optical property, 29, 46
- linear polarization, 15, 25, 55
- linear susceptibility, 22, 56
- linearity of photodetector, 387
- linearly polarized, 14
- lineshape
 - Gaussian, 231
 - homogeneously broadened, 226
 - inhomogeneously broadened, 230
 - Lorentzian, 35, 226
 - Voigt, 234
- lineshape function, 225, 230
 - homogeneously broadened, 226
 - inhomogeneously broadened, 230
- linewidth, 194
 - Doppler broadening, 231
 - homogeneous broadening, 226
 - inhomogeneous broadening, 231
 - laser mode, 283
 - lifetime broadening, 227
 - longitudinal mode, 210
 - mixed broadening, 234
 - natural broadening, 227
- linewidth enhancement factor, 294
- longitudinal mode, 207, 210, 280, 282
 - frequency spacing, 210, 219
 - of optical resonator, 207, 210
- longitudinal mode frequency, 210
- longitudinal mode width, 210
- longitudinal modulation, 297, 321, 323
- longitudinal modulator, 323
- longitudinal phase modulation, 323
- longitudinal phase modulator, 323
- Lorentz model, 33, 61
- Lorentz reciprocity theorem, 26, 142
- Lorentzian lineshape, 35, 226
- loss parameter, 286
 - output-coupling, 288
 - total, 288
- lower energy state, 32
- lower laser level, 250, 253, 255
- Mach–Zehnder interferometer, 178, 180
 - waveguide, 327
 - magnetic field, 4
- magnetic induction, 4
- magnetic material, 26
- magnetic permeability, 4
 - of free space, 4
- magnetic polarization, 4
- magnetically disordered, 50
- magnetically ordered, 49
- magnetization, 4, 7
 - spontaneous, 50
- magneto-optic amplitude modulation, 329

- magneto-optic effect, 49
 - first-order, 50, 328
 - linear, 50, 328
 - quadratic, 50
 - second-order, 50, 328
- magneto-optic Kerr effect, 52, 329
- magneto-optic modulation, 297, 320, 328
- magneto-optic modulator, 328
- magneto-optic phase modulation, 329
- material dispersion, 122, 126
- Maxwell's equations, 4–5, 11, 142
 - for plane wave normal mode, 73
 - for wave propagation, 68
 - in terms of mode field components, 68
- Maxwellian velocity distribution, 231
- mean square noise, 377
- mean square noise current, 385
- mean square noise voltage, 385
- metallic waveguide, 69
- Michelson interferometer, 178
- Michelson–Morley experiment, 178
- mixed broadening, 233
- modal dispersion, 115, 117, 122, 127
- mode coupling, 141
 - asymmetric, 144, 146, 160
 - between two modes, 147
 - codirectional, 154
 - contradirectional, 156
 - multiple-structure, 145
 - order, 150
 - phase-matched, 149, 161
 - phase-mismatched, 163
 - single-structure, 142
 - symmetric, 143, 160
- mode field
 - normalized, 71, 141
 - profile, 67
- mode index, 67
- mode locker, 352
- mode number, 109
- mode power, 131, 142
- mode volume, 287
- mode-order dispersion, 128
- mode-pulling effect, 277
- modulation
 - absorptive, 297, 305
 - all-optical, 340, 345, 350
 - external, 344
 - acousto-optic, 297, 320, 333
 - all-optical, 297, 320, 340, 342
 - absorptive, 340
 - dispersive, 340
 - refractive, 340
 - amplitude, 297–298, 305, 309, 320, 326, 344
 - acousto-optic, 334
 - analog, 305
 - digital, 305–306
 - electro-optic, 326
 - magneto-optic, 329
 - analog, 297–298, 306, 310, 314
 - current, 345
 - diffraction, 297, 299, 307, 333
 - digital, 297–298, 350
 - direct, 297, 299, 305, 308, 345
 - electro-absorption, 345
 - electro-optic, 297, 320
 - external, 297
 - absorptive, 344
 - refractive, 319
 - frequency, 297–298, 300, 309
 - analog, 300, 333
 - digital, 300, 333
 - longitudinal, 297, 321, 323
 - magneto-optic, 297, 320, 328
 - optical, 297
 - phase, 297–299, 306, 320, 344
 - analog, 299
 - differential, 302, 324, 326, 329
 - digital, 299
 - electro-optic, 321, 328
 - longitudinal, 323
 - magneto-optic, 329
 - transverse, 322
 - polarization, 297, 302, 306, 324
 - acousto-optic, 333
 - analog, 302
 - digital, 302
 - electro-optic, 324
 - magneto-optic, 329
 - refractive, 297, 300, 305, 307
 - all-optical, 340
 - electro-optic, 320
 - external, 319
 - magneto-optic, 329
 - small-signal, 316
 - spatial, 297, 299, 307
 - transverse, 297, 321, 323
- modulation bandwidth
 - 3-dB, 311, 317
 - of LED, 311
 - of semiconductor laser, 317
- modulation current, 308, 311, 316
- modulation depth, 306, 322
- modulation frequency, 311, 316, 339
- modulation index, 310, 316
- modulation power spectrum
 - of LED, 311
 - of semiconductor laser, 317
- modulation response, 308
 - of LED, 311
 - of semiconductor laser, 316
- modulation scheme, 297–298
- modulation signal, 308
- modulator
 - acousto-optic
 - standing-wave, 338
 - traveling-wave, 336
 - amplitude, 326
 - bulk, 297
 - electro-absorption, 345, 349
 - electro-optic, 320
 - external, 306
 - longitudinal, 323
 - magneto-optic, 328
 - phase, 322–323
 - polarization, 326
 - transverse, 322
 - waveguide, 297
 - momentum dispersion, 23
- momentum relaxation time, 38
- monochromatic optical wave, 13, 20, 73
- multimode waveguide, 118
- natural broadening, 227
- Nd:glass, 233
- Nd:YAG, 233
- Nd:YAG laser, 258
- NEA, 367, *See* negative electron affinity
- Néel temperature, 49
- negative electron affinity, 367
- NEP, 384, *See* noise equivalent power
- noise, 225
 - Johnson, 375
 - mean square, 377, 385
 - Nyquist, 375
 - of photodetector, 375
 - quantum, 375
 - shot, 375–376
 - thermal, 375, 379
- noise equivalent power, 384
- noncentrosymmetric, 46, 58
- nondegenerate semiconductor, 365
- nonlinear carrier relaxation rate, 315
- nonlinear gain parameter, 315
- nonlinear optical amplifier, 265
- nonlinear optical property, 29
- nonlinear optical susceptibility, 55
- nonlinear polarization, 55
 - second-order, 55
 - third-order, 55
- nonlinear susceptibility, 56
 - n*th-order, 56
 - second-order, 59
 - third-order, 59
- nonmagnetic material, 26
- nonplanar optical structure, 66
 - dielectric, 70
- nonplanar waveguide, 66, 108
 - dielectric, 69, 108
- nonradiative relaxation rate, 226

- nonreciprocal, 51–52, 331
- nonreciprocal medium, 26
- normal dispersion, 36, 122
- normal incidence, 96
- normal mode
 - acoustic, 53
 - basis for linear expansion, 72, 141
 - coupling, 141
 - degenerate, 67
 - extraordinary wave, 81
 - field profile, 67
 - Gaussian, 86
 - guided, 109, 112
 - fundamental, 109, 121
 - high-order, 109
 - number, 109
 - hybrid, 69
 - index, 67
 - intensity distribution, 71
 - interface, 92
 - of planar interface, 98
 - of propagation, 66, 73
 - ordinary wave, 81
 - orthogonality relation, 71
 - orthonormality relation, 71
 - plane wave, 73, 78, 83
 - power, 71
 - principal polarization, 25
 - propagation constant, 67
 - radiation, 98
 - substrate radiation, 111–112
 - substrate–cover radiation, 111, 113
 - super, 145
 - surface plasmon, 104
 - transverse electric, TE, 69
 - transverse electromagnetic, TEM, 69
 - transverse magnetic, TM, 69
 - waveguide, 107
- normal mode field pattern, 67
- normal state, 32
- normalized frequency and waveguide thickness, 112
- normalized guide index, 112
- normalized mode field, 71, 141
- normalized transmittance, 193, 208
 - of Fabry–Pérot interferometer, 193
 - of optical cavity, 208
- Nyquist noise, 375
- on-off keying, 305
- OOK, 305, *See* on-off keying
- optical activity, 30
 - magnetically induced, 30
 - natural, 30
- optical amplification, 129, 225, 244, 265
- optical amplifier, 265
- optical anisotropy, 24, 29
- optical attenuation, 129, 225, 244
- optical axis, 28, 77, 81
- optical carrier, 3, 12, 19, 123
- optical cavity, 204, 209
- optical conductivity, 38
- optical confinement, 108
- optical discriminator, 352
- optical energy, 8
 - density, 9
- optical feedback, 204, 274
- optical field
 - angular frequency, 20
 - complex, 12, 18, 169
 - frequency, 18
 - harmonic, 12
 - magnitude, 18
 - phase, 18, 169
 - polarization, 18
 - real amplitude, 19
 - scalar complex amplitude, 18
 - vectorial complex amplitude, 18
 - wavevector, 18
- optical-field-induced birefringence, 342
- optical frequency, 1
- optical gain, 23, 129
- optical gain coefficient, 259
- optical grating, 183, 307
- optical interference, 169
- optical interferometer, 178
- optical Kerr effect, 342
- optical loss, 23, 129
 - distributed, 218
- optical medium
 - anisotropic, 24
 - isotropic, 24
 - linear, 24
 - lossless, 26
 - lossy, 26
 - nonmagnetic, 26
 - nonreciprocal, 26
 - optically active, 26
 - reciprocal, 26
- optical modulation, 297
- optical noise, 225
- optical nonlinearity, 55
- optical path length, 176
 - round-trip, 206
- optical power, 8, 131, 363
- optical property
 - linear, 29, 46
 - nonlinear, 29
- optical pumping, 254
- optical resonance, 204
- optical resonator, 204
- optical soliton, 342
- optical spectrum analyzer, 195
- optical switching, 298
- optical thin film, 196
- optical transition, 224
- optical wave
 - monochromatic, 13, 20
 - plane, 13, 19
- optical wavelength
 - in free space, 1
 - in homogeneous medium, 76
- order of coupling, 150
- order of diffraction, 184
- ordinary index, 28
- ordinary wave, 81
- orientation, 14
- orthogonal polarizations, 17
- orthogonality relation
 - of normal mode, 71
- orthonormality relation
 - of Gaussian mode, 87
 - of normal mode, 71
- output-coupling loss parameter, 288
- output-coupling rate, 288
- overlap coefficient, 146
- overlap factor, 206, 327
- p polarized, π polarized, 95
- p wave, π wave, 95
- parallel polarization, 95
- paramagnetic material, 49
- paraxial approximation, 87
- Parseval’s theorem, 408
- passive cavity, 207
- perfect phase matching, 153, 161–162, 165, 334
- periodic index modulation, 151
- periodic perturbation, 150
- periodic structural corrugation, 151
- permittivity, 7, 39, 122
 - acousto-optically induced change, 333
 - electric field-dependent, 44
 - frequency domain, 13, 23
 - magnetic field-dependent, 44
 - magnetization-dependent, 50
 - momentum space, 13, 23
 - of gain medium, 218
 - optical, 22
 - optical field-dependent, 341
 - photoelastic, 54
 - principal, 27
 - real space, 7, 23
 - rotation field-dependent, 54
 - scalar, 66
 - strain field-dependent, 54
 - tensor, 7
 - time domain, 7, 23
 - total, 39
- perpendicular polarization, 95
- perturbing polarization, 142

- phase matched, 156, 158, 160
- phase matching, 160, 165, 183, 187, 334, 336
 - perfect, 153, 161–162, 165, 334
- phase mismatch, 149, 151, 160, 163, 165, 185, 306
- phase modulation, 297–299, 306, 320, 344
 - all-optical, 342
 - analog, 299
 - cross, 342
 - depth, 322
 - differential, 302, 324, 326, 329
 - digital, 299
 - electro-optic, 321, 328
 - longitudinal, 323
 - magneto-optic, 329
 - self, 342
 - transverse, 322
- phase relaxation, 250
- phase relaxation rate, 225
- phase retardation, 324
- phase velocity, 122
 - of waveguide mode, 127
- phase-matched coupling, 149, 161
- phase-matching condition, 160, 186, 188, 190–191, 307, 333
 - for down-shifted Bragg diffraction, 335
 - for up-shifted Bragg diffraction, 335
- phase-mismatched coupling, 163
- phase-shift keying, 298, *See* PSK
 - binary. *See* BPSK
 - quadrature. *See* QPSK
- phase-velocity dispersion, 122
- photocathode, 362–363
- photoconductive detector, 368
- photoconductive mode, 373–374
- photoconductivity, 368
 - extrinsic, 369
 - intrinsic, 369
- photoconductor, 363
 - extrinsic, 369
 - intrinsic, 369
- photocurrent, 363, 372
 - reverse, 372
- photodetector, 362
- photodetector bandwidth, 385
 - intrinsic, 389
 - RC, 389
- photodiode, 371
 - junction, 363, 371
 - vacuum, 362
- photoelastic coefficient, 53
- photoelastic effect, 53
 - dynamic, 53
- photoelastic permittivity tensor, 54
- photoelectric effect, 362
 - external, 362–363
 - internal, 362
- photoelectron, 363
- photoemission, 363
 - from degenerate semiconductor, 365
 - from metal, 365
 - from NEA photocathode, 367
 - from nondegenerate semiconductor, 365
- photoemissive detector, 363
- photoemissive device, 362
- photomultiplier tube, 362
- photon, 1
 - energy, 1
 - flux, 2
 - flux density, 2
 - momentum, 1
 - number, 363
 - speed, 1
- photon detector, 362
- photon lifetime, 214
 - of Fabry–Pérot cavity, 219
- photothermal effect, 362
- phototransistor, 363
- photovoltaic device, 363
- photovoltaic mode, 373
- P–I* characteristics
 - of LED, 310
- planar dielectric waveguide, 108
- planar interface, 66, 92
- planar optical structure, 66
 - dielectric, 70
- planar waveguide, 66, 108
 - dielectric, 69
 - metallic, 69
- Planck’s formula, 235
- plane of incidence, 94
- plane polarized, 14
- plane wave, 13, 19, 73
 - normal mode, 73, 78, 83
 - basis for linear expansion, 74, 76, 78, 84
- plasma frequency, 40, 104
 - surface, 106
- PM, 298, *See* phase modulation
- p–n homojunction, 371
- Pockels coefficient, 45, 59
- Pockels effect, 45
- point group, 46, 58
- Poisson probability distribution, 377
- polar semiconductor, 29
- polar vector, 6
- polarization, 4, 7
 - circular, 16, 25
 - elliptic, 14, 25
 - ellipticity, 14
 - left-circular, 16
 - linear, 15, 25, 55
 - nonlinear, 55
 - n*th-order, 56
 - second-order, 55
 - third-order, 55
 - of optical field, 13
 - orientation, 14
 - orthogonality relation, 17, 74
 - principal state, 25
 - right-circular, 16
 - state, 16
 - unit vector, 17
- polarization dispersion, 117, 122, 127
- polarization modulation, 297, 302, 306, 324
 - acousto-optic, 333
 - all-optical, 342
 - analog, 302
 - digital, 302
 - electro-optic, 324
 - magneto-optic, 329
- polarization modulator, 326
- polarization-mode dispersion, 128
- polarization-shift keying, 302, *See* PolSK
 - binary. *See* BPolSK
- polarizer, 326
- polarizing beam splitter, 85
- PolSK, 302, *See* polarization-shift keying
- population
 - density, 32, 249, 253
 - distribution, 33
- population decay rate, 33
- population difference, 34, 244
- population inversion, 33, 242, 249, 251, 255
 - condition, 252
 - effective, 250
 - effective condition, 252
- population relaxation, 250
- power, 2
 - of normal mode, 71, 142
- power conversion efficiency, 291
 - differential, 291
- power density, 10
- power gain, 207, 265
 - small-signal, 265
 - unsaturated, 265
- power theorem, 408
- power–current characteristics
 - of LED, 309
 - of semiconductor laser, 314
- Poynting vector, 9, 71, 73
 - complex, 12
 - time-averaged, 12
- principal axis, 27, 29, 78
- principal dielectric axis, 27, 46, 48
- principal dielectric constant, 28

- principal dielectric susceptibility, 28
 principal index of refraction, 28, 46, 48
 principal normal mode, 25, 48, 78
 principal permittivity, 27, 78
 principal polarization state, 25
 principle of detailed balance, 236
 probability density function, 230
 propagation constant, 19, 67, 75
 complex, 129, 131
 of extraordinary wave, 82
 of Gaussian normal mode, 87
 of guided mode, 109, 113
 of normal mode, 67
 of ordinary wave, 82
 of principal normal mode, 28, 78
 of substrate radiation mode, 111, 113
 of substrate–cover radiation mode, 111, 113
 of surface plasmon mode, 106
 of waveguide mode, 126, 131
 propagation direction, 19, 76
 PSK, 298–299, *See* phase-shift keying
 pump power
 threshold, 287
 transparency, 287
 pumping, 249, 254
 pumping rate, 250, 253
 transparency, 257
 pumping ratio, 287
 pumping requirement, 254–256
 minimum, 255–256, 260
 pumping technique, 249
 push–pull operation, 327
- Q switch, 352
 QFSK. *See* quadrature frequency-shift keying
 QPSK. *See* quadrature phase-shift keying
 quadrature frequency-shift keying, 300
 quadrature phase-shift keying, 300
 quality factor, 214
 of cold cavity, 214
 quantum detector, 362
 quantum efficiency, 368, 371, 377
 external, 309, 363, 382
 internal, 382
 of photodetector, 382
 pump, 262
 quantum noise, 375
 quantum regime, 380
 quantum-confined Stark effect, 345
 quantum-well structure, 347
 quarter-wave plate, 80
 quasi-two-level system, 254, 259
- radiation mode, 98
 of planar interface, 98
 one-sided, 99
 substrate, 111
 substrate–cover, 111
 two-sided, 101
 radiative relaxation rate, 226
 Raman–Nath diffraction, 334
 rate equations, 250
 for semiconductor laser, 313
 Rayleigh range, 88
 reality condition, 24, 56
 reciprocal, 51–52
 reciprocal medium, 26
 rectangular function, 406
 reflectance, 95–96
 of Fabry–Pérot interferometer, 193
 reflection, 93
 external, 96
 internal, 96
 partial, 101
 total, 97, 99
 reflection coefficient, 95
 of contradirectional coupling, 158
 reflection-type polarizer, 97
 reflectivity, 95
 of contradirectional coupling, 158
 refraction, 93
 double, 98
 refractive external modulation, 319
 refractive index, 19, 76, *See* index of refraction
 effective for waveguide mode, 112, 126
 refractive modulation, 297, 300, 305, 307
 all-optical, 340
 electro-optic, 320
 external, 319
 magneto-optic, 329
 relative impermeability tensor, 45, 53
 relaxation oscillation, 316
 relaxation rate, 32
 carrier. *See* carrier relaxation rate
 nonradiative, 226
 optical polarization, 33
 phase, 225, 250
 population, 33, 250
 radiative, 226
 susceptibility, 33
 total, 226
 relaxation resonance frequency, 316
 resonance condition
 of optical cavity, 209, 211
 for Gaussian mode, 212
 for waveguide mode, 212
 transverse
 for waveguide mode, 109
 resonance frequency, 32, 204
 of cold Fabry–Pérot cavity, 218
 of optical cavity, 204, 211
 transition, 33, 224–225
 resonant interaction, 32
 resonant laser transition, 218, 275
 resonant optical cavity, 204
 resonant optical susceptibility, 32, 243
 resonant susceptibility tensor, 33
 resonant transition, 224
 response speed of a photodetector, 389
 responsivity, 380, 383
 intrinsic, 384
 spectral, 367, 371, 384
 reverse current, 372
 reverse-coupling matrix, 157, 161
 right-circular polarization, 16
 ring cavity, 204, 206, 212
 ring laser, 275
 risetime, 389
 rotating-wave approximation, 34
 rotation tensor, 53
 rotation-optic coefficient, 53
 rotatory power, 330
 round-trip amplification factor, 207, 274
 round-trip gain factor, 207, 274
 mode-dependent, 275
 of cold cavity, 214
 of cold Fabry–Pérot cavity, 218
 round-trip optical path length, 206, 212
 round-trip phase shift, 192–193, 207, 209, 274
 mode-dependent, 211, 217, 275
 of Gaussian mode, 218
 round-trip time, 205, 210
 ruby laser, 258
- s polarized, σ polarized, 95
 s wave, σ wave, 95
 saturable absorber, 351
 saturated gain parameter, 287
 saturation intensity, 259, 351
 saturation lifetime, 259–260
 saturation output power, 288
 saturation photon density, 287
 saturation power, 265
 scalar field amplitude, 18
 Schawlow–Townes limit, 284
 Schawlow–Townes relation, 284
 self defocusing, 342
 self focusing, 342
 self modulation, 340
 self-phase modulation, 342
 semiconductor
 degenerate, 365
 direct-gap, 249, 346, 369
 extrinsic, 369
 group IV, 367

- semiconductor (cont.)
 - III–V, 29, 367
 - indirect-gap, 346, 369
 - nondegenerate, 365
 - polar, 29
- semiconductor laser, 308, 313
- semiconductor photodiode, 371
- shot noise, 375–376
 - excess, 378
 - of photodetector, 378
 - of photodetector with internal gain, 378
- shot-noise limited, 380
- signal current, 372
 - of photodetector, 363
- signal-to-noise ratio, 376, 379
 - current, 376
 - power, 376
 - voltage, 376
- single-mode waveguide, 118, 121
- slab waveguide, 111
 - symmetric, 119
- slope efficiency, 291
- slow axis, 80
- slowly varying amplitude, 56
- small-signal gain coefficient, 263
- small-signal modulation, 316
- small-signal power gain, 265
- Snell’s law, 95
- SNR, 376, *See* signal-to-noise ratio
- space inversion, 6, 51, 59
 - transformation, 6, 46
- spatial beam walk-off, 84
- spatial light filter, 352
- spatial modulation, 297, 299, 307
- spatially coherent, 173
- spatially incoherent, 173
- specific detectivity, 369, 386
 - of photoconductive detector, 369
- specific Faraday rotation, 330
- spectral broadening, 225, 342
 - dephasing, 228
 - Doppler, 231
 - homogeneous, 225
 - inhomogeneous, 230
 - lifetime, 226
 - mixed, 233
 - natural, 227
- spectral detectivity, 382
 - of photodetector, 382
- spectral hole burning, 282
- spectral intensity distribution, 234
- spectral lineshape, 225
- spectral response, 367, 382
- spectral responsivity, 371, 382, 384
 - of photocathode, 367
 - of photodetector, 382
 - of photodiode, 371
- speed of light
 - in free space, 1, 75
 - in homogeneous medium, 76
- spontaneous carrier recombination
 - lifetime, 309
- spontaneous carrier recombination rate, 309
- spontaneous carrier relaxation rate, 315
- spontaneous emission, 224, 267
 - amplified, 269
- spontaneous emission factor, 284
- spontaneous emission power, 268
- spontaneous emission power density, 268
- spontaneous emission rate, 234
- spontaneous emission spectrum, 234
- spontaneous magnetization, 50
- spontaneous radiative lifetime, 226, 236
- spontaneous transition, 236
- spontaneous transition rate, 235
- spot size, 86
- square-law detector, 362
- square-pulse response, 389
- stability criterion
 - for Fabry–Pérot cavity, 216
- standing wave, 182
- step-index waveguide, 108
 - planar, 111
- stimulated emission, 35, 224
- stimulated-emission transition, 236
- strain
 - shear, 53
 - tensile, 53
- strain tensor, 53
- strain-optic coefficient, 53
- substrate radiation mode, 111–112
- substrate–cover radiation mode, 111, 113
- super mode, 145
- super structure, 145
- surface grating, 189
- surface plasma frequency, 106
- surface plasmon mode, 104
 - cutoff frequency, 106
 - cutoff wavelength, 106
 - dispersion curve, 106
 - propagation constant, 106
- susceptibility, 7, 122
 - conduction, 39
 - electric field-dependent, 44
 - frequency domain, 7, 13, 23
 - linear, 22, 56
 - magnetic field-dependent, 44
 - magnetization-dependent, 50
 - momentum space, 7, 13, 23
 - nonlinear, 56
 - n*th-order, 56
 - second-order, 59
 - third-order, 59
- nonlinear optical, 55
- optical, 22
- principal, 28
- real space, 23
- resonant, 32, 243
- rotation field-dependent, 54
- strain field-dependent, 54
- tensor, 7, 33
- time domain, 23
- switching
 - all-optical, 340
 - optical, 298
- symmetric coupling, 143, 160
- symmetric waveguide, 112, 118–119, 121
 - slab, 119
- TE mode, 69, 76, 114, 119, 121
- TE polarization, 95
- TEM mode, 69, 87, 108
- TEM wave, 75
- temporal beat, 173
- temporally coherent, 173
- temporally incoherent, 173
- thermal detector, 362
- thermal equilibrium, 32, 235, 249
- thermal noise, 375, 379
 - of photodetector, 379
- thermal regime, 380
- thermal-noise limited, 380
- three-level system, 255, 259–260
- threshold carrier density, 314
- threshold condition, 286
 - for semiconductor laser, 314
- threshold current density, 314
- threshold gain coefficient, 276, 280
- threshold gain parameter, 286, 314
- threshold injection current, 314
- threshold intracavity energy growth rate, 286
- threshold photon energy, 363, 368
 - of extrinsic photoconductivity, 369
 - of intrinsic photoconductivity, 369
 - of photoemission
 - from degenerate semiconductor, 365
 - from metal, 365
 - from NEA photocathode, 367
 - from nondegenerate semiconductor, 365
 - of semiconductor photodiode, 371
- threshold pump power, 276, 287
- threshold pumping level, 276
- threshold wavelength, 363, 368
- Ti:sapphire, 239
- time reversal, 6, 51
 - transformation, 6, 50
- TM mode, 69, 76, 108, 115, 119, 121
- TM polarization, 95

total carrier relaxation rate, 316	transverse magnetic mode. <i>See</i> TM mode	evanescent radiation mode, 111
total internal reflection, 97, 99	transverse mode, 211, 280, 282	graded-index, 108
total relaxation rate, 226	of optical resonator, 211	guided mode, 109, 112
transition	transverse modulation, 297, 321, 323	cutoff condition, 117, 121
absorption, 236	transverse modulator, 322–323	cutoff frequency, 117
band-to-band, 37	transverse phase modulation, 322	cutoff wavelength, 117
energy, 236	transverse phase modulator, 322	fundamental, 109, 118, 121
induced, 224	triangular function, 406	high-order, 109
interband, 37	two-level system, 253	number, 109, 118, 121
intraband, 38	quasi, 254, 259	TE, 114, 119, 121
laser, 218, 275	uniaxial crystal, 28, 77, 81	TM, 115, 119, 121
optical, 224	negative, 28	metallic, 69
resonance frequency, 33, 224	positive, 28	mode, 107
resonant, 224	uniform perturbation, 149	effective refractive index, 112
spontaneous, 236	unit polarization vector, 17	multimode, 118
stimulated-emission, 236	unsaturated absorption coefficient, 351	nonplanar, 66, 108
transition cross section, 238	unsaturated gain coefficient, 259–260, 263	dielectric, 69
transition rate, 234	unsaturated gain parameter, 286	planar, 66, 108
absorption, 234	unsaturated power gain, 265	cover, 108
induced, 235	upper energy state, 32	dielectric, 69
induced downward, 234	upper laser level, 250, 253, 255	film, 108
spontaneous, 235	population, 257, 267	metallic, 69
spontaneous emission, 234	transparency population density, 257	step-index, 111
stimulated emission, 234	V number, 112	substrate, 108
upward transition, 234	vacuum energy level, 363	single-mode, 118, 121
transition resonance frequency, 33, 224–225	vacuum photodiode, 362	slab, 111
transmission coefficient, 95	valence electron, 32	symmetric, 119
transmission efficiency, 382	vectorial field amplitude, 18	step-index, 108
transmission grating, 183	Verdet constant, 330	substrate radiation mode, 111–112
transmission line, 69	Voigt lineshape, 234	substrate–cover radiation mode, 111, 113
transmissive diffraction grating, 183–184	walk-off angle, 84	symmetric, 112, 118–119, 121
transmissivity, 95	wave equation, 10–11	V number, 112
transmittance, 95–96	for plane wave normal mode, 74	weakly guiding, 117
normalized, 193, 208	wavefront, 19, 73	waveguide dispersion, 122, 126
of Fabry–Pérot interferometer, 193	waveguide	waveguide modulator, 297
transparency, 257, 260	asymmetric, 118	wavelength
transparency population density, 257	asymmetry factor, 112	acoustic, 52
transparency pump power, 276, 287	cladding, 108	optical, 1, 76
transparency pumping rate, 257	core, 108	wavenumber, 19, 76, 130
transverse electric mode. <i>See</i> TE mode	dielectric, 108	wavevector, 1, 73
transverse electromagnetic mode. <i>See</i> TEM mode		weakly guiding waveguide, 117